ATM3400NSA

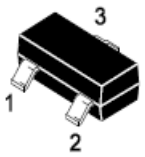
N-Channel Enhancement Mode Field Effect Transistor

Drain-Source Voltage: 30V ***Drain Current: 5.8A***

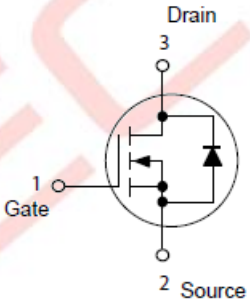
Features

- Trench FET Power MOSFET
- Excellent $R_{DS(on)}$ and Low Gate Charge
- $R_{DS(ON)}$ < 35mΩ (V_{GS} = 10V)
- $R_{DS(ON)}$ < 40mΩ (V_{GS} = 4.5V)
- $R_{DS(ON)}$ < 52mΩ (V_{GS} = 2.5V)

SOT-23



1 Gate 2 Source 3 Drain



Application

- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch

Absolute maximum ratings (Ta=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current	I_D	5.8	A
Pulsed Drain Current[1)]	I_{DM}	30	A
Power Dissipation	P_D	0.35	W
Thermal Resistance from Junction to Ambient[2)]	$R_{\theta JA}$	357	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55~ +150	℃

Electrical characteristics (T_A=25 °C, unless otherwise noted)

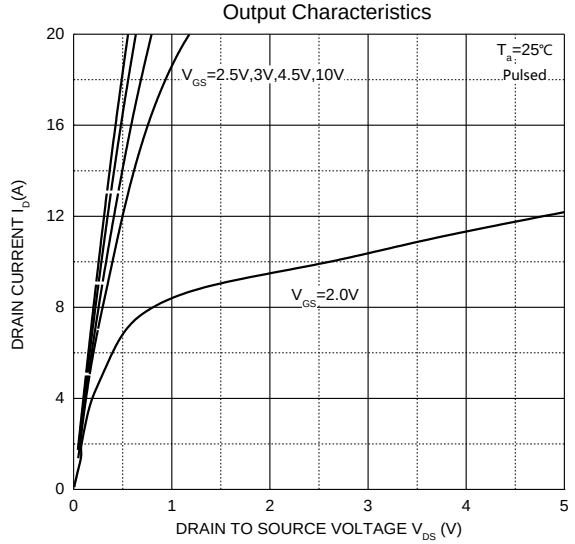
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =250μA	30			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =24V,V_{GS} = 0V			1	μA
Gate-body leakage current	I_{GSS}	V_{GS} =±12V, V_{DS} = 0V			±0.1	μA
Gate threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250μA	0.7		1.4	V
Drain-source on-resistance[3]	$R_{DS(on)}$	V_{GS} =10V, I_D =5.8A		27	35	mΩ
		V_{GS} =4.5V, I_D =5A		29	40	
		V_{GS} =2.5V, I_D =4A		38	52	
Forward transconductance	g_{FS}	V_{DS} =5V, I_D =5A	8			S
Dynamic characteristics[4]						
Input Capacitance	C_{iss}	V_{DS} =15V,V_{GS} =0V,f =1MHz			1050	pF
Output Capacitance	C_{oss}			99		
Reverse Transfer Capacitance	C_{rss}			77		
Gate resistance	R_g	V_{DS} =0V,V_{GS} =0V, f =1MHz			3.6	Ω
Switching Characteristics[4]						
Turn-on delay time	$t_{d(on)}$	V_{GS}=10V,V_{DS}=15V, R_L=2.7Ω,R_{GEN}=3Ω			5	ns
Turn-on rise time	t_r				7	
Turn-off delay time	$t_{d(off)}$				40	
Turn-off fall time	t_f				6	
Source-Drain Diode characteristics						
Diode Forward voltage[3]	V_{DS}	V_{GS} =0V, I_S=1A		0.7	1.3	V

Note:

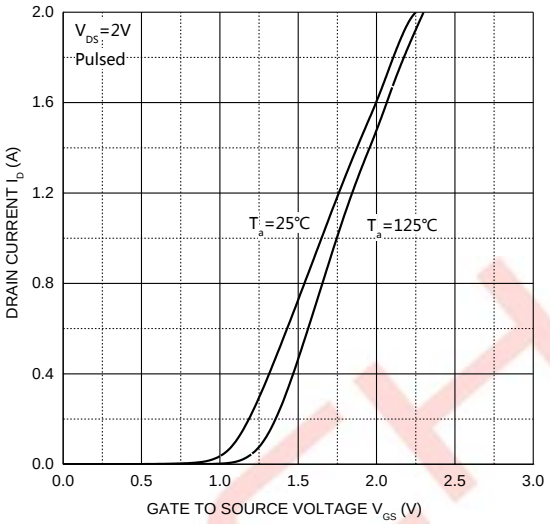
1) Repetitive Rating : Pulse width limited by maximum junction temperature.
2) Surface Mounted on FR4 Board, t < 5 sec.
3) Pulse Test : Pulse Width≤300μs, Duty Cycle ≤ 2%.
4) Guaranteed by design, not subject to production testing.

Typical Characteristics Curves

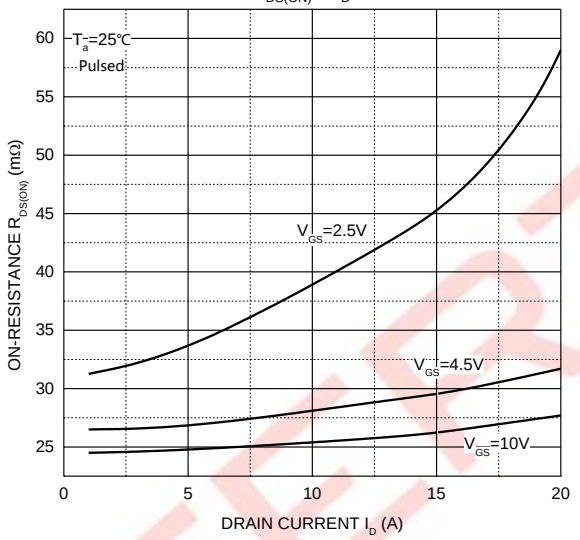
Output Characteristics



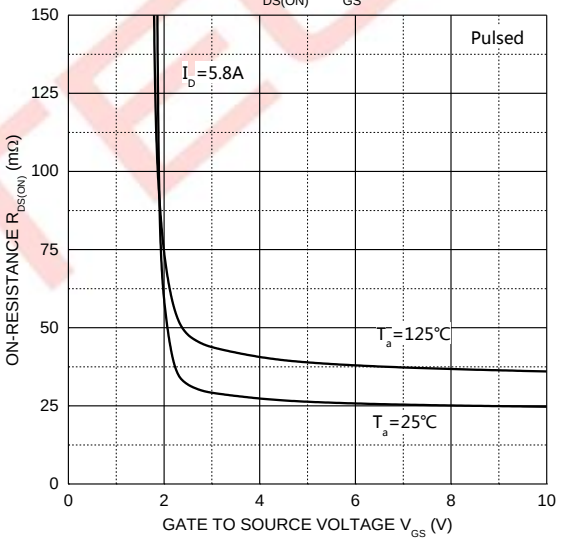
Transfer Characteristics



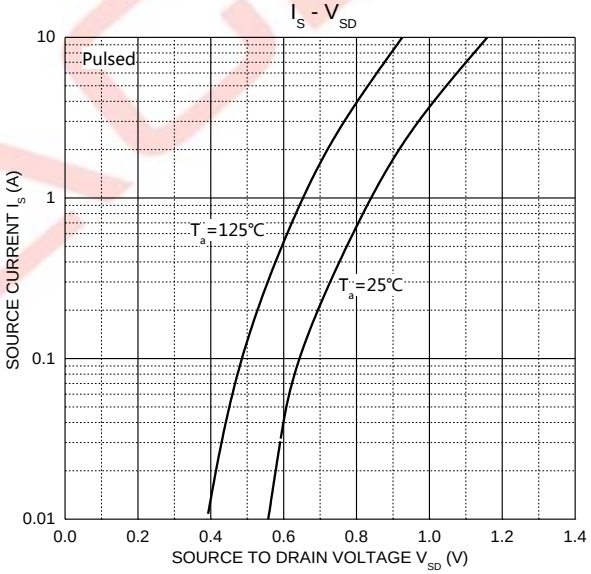
$R_{DS(ON)}$ – I_D



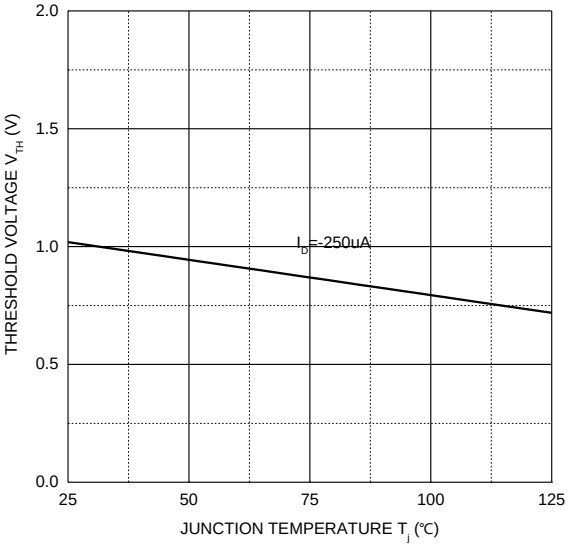
$R_{DS(ON)}$ - V_{GS}



I_S - V_{SD}

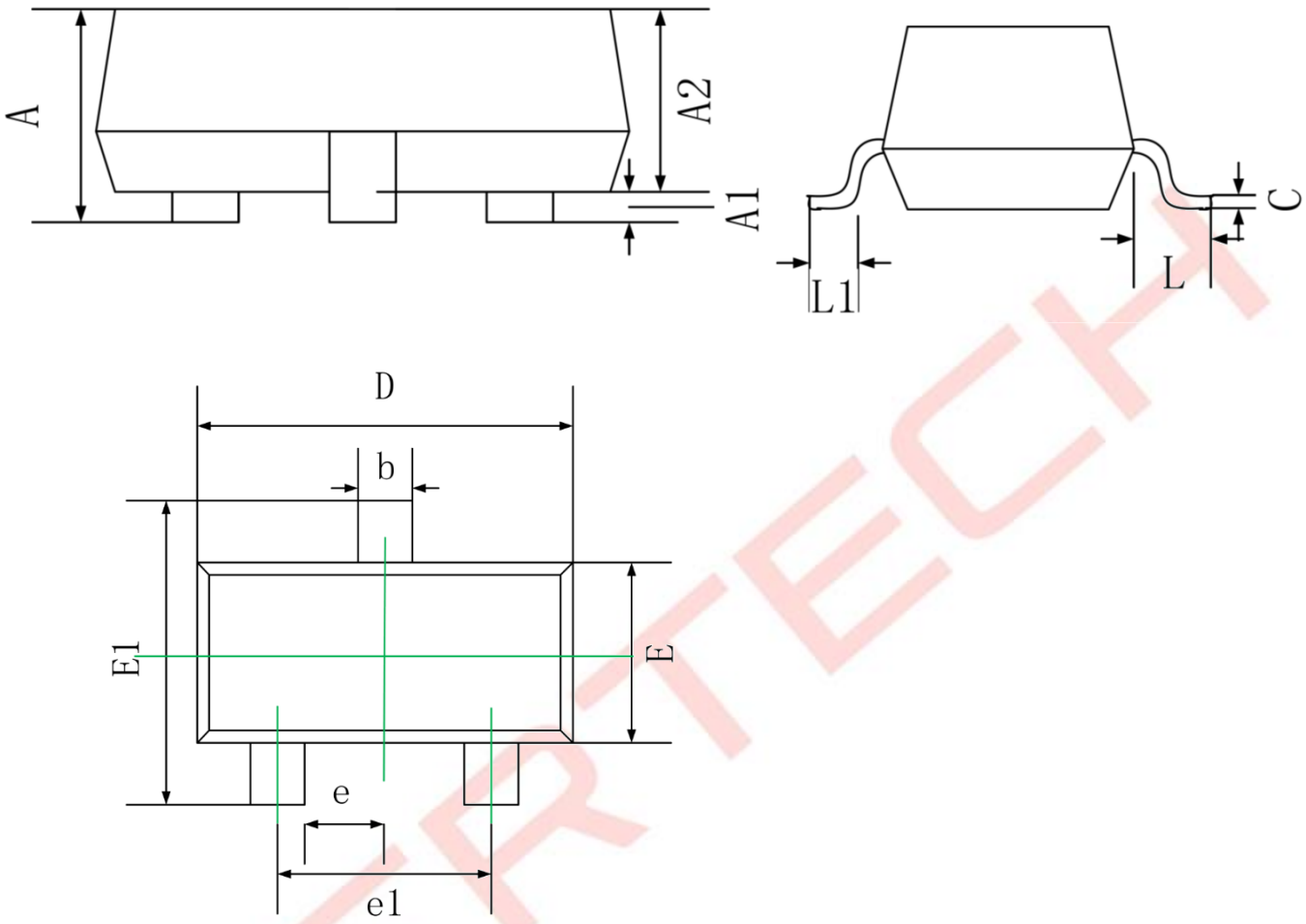


Threshold Voltage



Package Outline

SOT-23



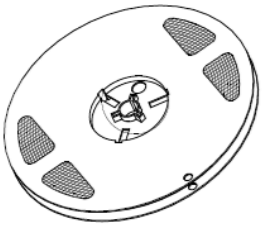
Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.90	1.15
A1	0.00	0.10
A2	0.90	1.05
b	0.30	0.50
c	0.08	0.15
D	2.80	3.00
E	1.20	1.40
E1	2.25	2.55
e	0.95 REF.	
e1	1.80	2.00
L	0.55 REF.	
L1	0.30	0.50

Package Specifications

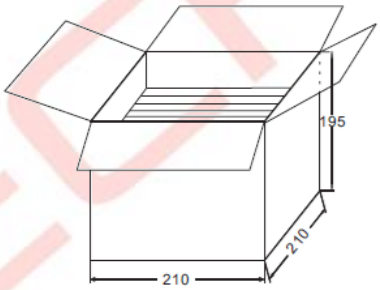
◆ **The method of packaging**

SOT-23 (TO-236)

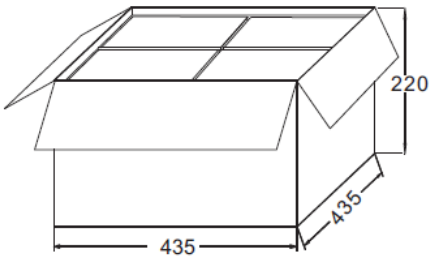
3,000 pcs per reel



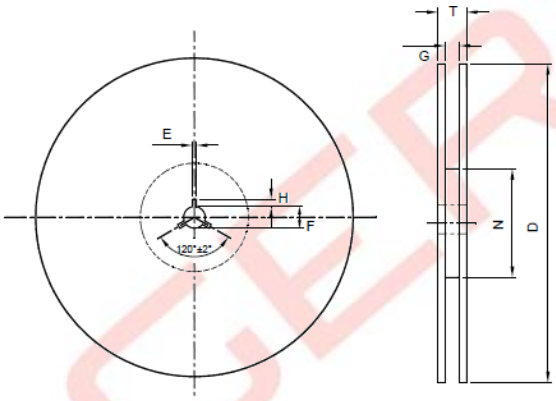
30,000 pcs per box
10 reels per box



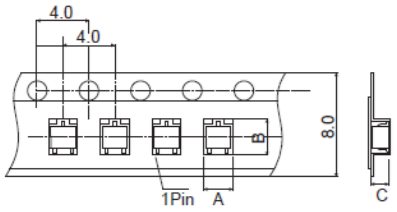
120,000 pcs per carton
4 boxes per carton



◆ **Embossed tape and reel data**



Reel (7")



Tape (8mm)

Symbol	Value (unit: mm)
A	3.15 ± 0.1
B	2.7 ± 0.1
C	1.25 ± 0.1
E	2 ± 0.5
F	13 ± 0.5
D	178 ± 2.0
G	8.4 ± 1.5
H	4 ± 0.5
N	60
T	< 14.9

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